

NLAST44599

Low Voltage Single Supply Dual DPDT Analog Switch

The NLAST44599 is an advanced CMOS dual-independent DPDT (double pole-double throw) analog switch, fabricated with silicon gate CMOS technology. It achieves high-speed propagation delays and low ON resistances while maintaining CMOS low-power dissipation. This DPDT controls analog and digital voltages that may vary across the full power-supply range (from V_{CC} to GND).

The device has been designed so the ON resistance (R_{ON}) is much lower and more linear over input voltage than R_{ON} of typical CMOS analog switches.

The channel-select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The NLAST44599 can also be used as a quad 2-to-1 multiplexer-demultiplexer analog switch with two Select pins that each controls two multiplexer-demultiplexers.

- Select Pins Compatible with TTL Levels
- Channel Select Input Overvoltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break-Before-Make Circuitry
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^\circ C$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch-up Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;
Machine Model > 200 V
- Chip Complexity: 158 FETs
- Pb-Free Packages are Available



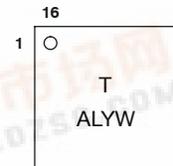
ON Semiconductor®

<http://onsemi.com>

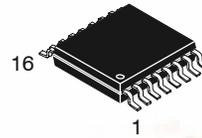
MARKING DIAGRAMS



QFN-16
MN SUFFIX
CASE 485G



(TOP VIEW)



TSSOP-16
DT SUFFIX
CASE 948F



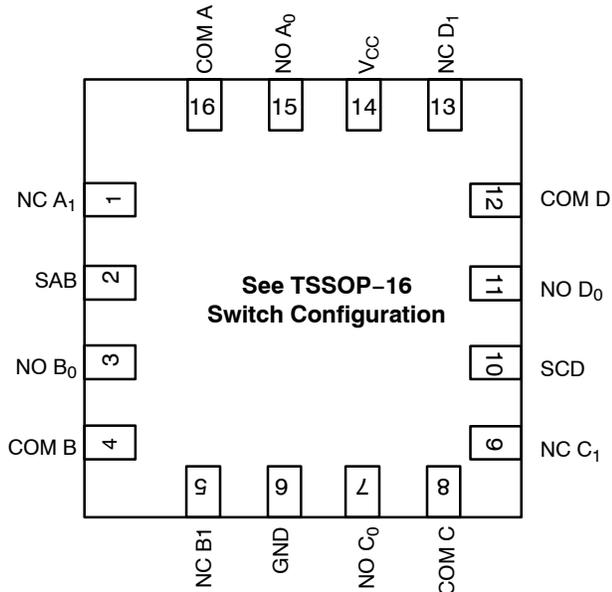
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

NLAST44599

QFN-16 PACKAGE



FUNCTION TABLE

| Select AB or CD | ON Channel |
|-----------------|------------|
| L | NC to COM |
| H | NO to COM |

TSSOP-16 PACKAGE

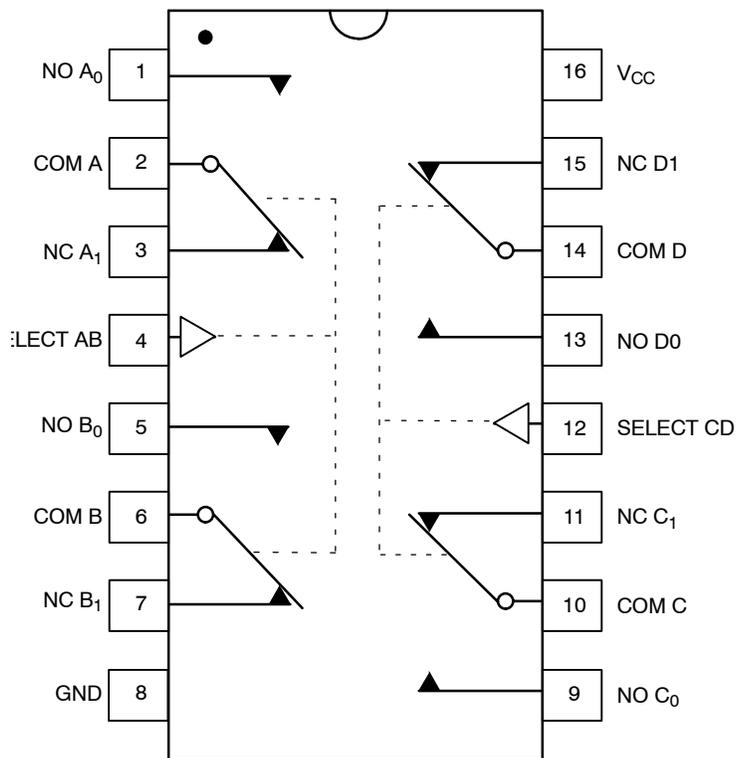


Figure 1. Logic Diagram

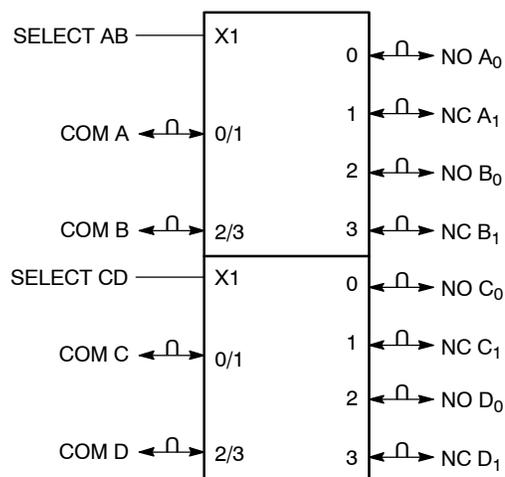


Figure 2. IEC Logic Symbol

NLAST44599

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit | |
|-----------------------|---|---|------|------|
| V _{CC} | Positive DC Supply Voltage | -0.5 to +7.0 | V | |
| V _{IS} | Analog Input Voltage (V _{NO} or V _{COM}) | -0.5 ≤ V _{IS} ≤ V _{CC} + 0.5 | V | |
| V _{IN} | Digital Select Input Voltage | -0.5 ≤ V _I ≤ +7.0 | V | |
| I _{IK} | DC Current, Into or Out of Any Pin | ±50 | mA | |
| P _D | Power Dissipation in Still Air | QFN-16 | 800 | mW |
| | | TSSOP-16 | 450 | |
| T _{STG} | Storage Temperature Range | -65 to +150 | °C | |
| T _L | Lead Temperature, 1 mm from Case for 10 Seconds | 260 | °C | |
| T _J | Junction Temperature Under Bias | +150 | °C | |
| MSL | Moisture Sensitivity | Level 1 | | |
| F _R | Flammability Rating | Oxygen Index: 30% - 35% UL-94-VO (0.125 in) | | |
| V _{ESD} | ESD Withstand Voltage | Human Body Model (Note 1) | 2000 | V |
| | | Machine Model (Note 2) | 200 | |
| | | Charged Device Model (Note 3) | 1000 | |
| I _{LATCH-UP} | Latch-Up Performance | Above V _{CC} and Below GND at 125°C (Note 4) | ±300 | mA |
| θ _{JA} | Thermal Resistance | QFN-16 | 80 | °C/W |
| | | TSSOP-16 | 164 | |

Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

1. Tested to EIA/JESD22-A114-A.
2. Tested to EIA/JESD22-A115-A.
3. Tested to JESD22-C101-A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit | |
|---------------------------------|------------------------------------|---------------------------------|-----------------|------|------|
| V _{CC} | DC Supply Voltage | 2.0 | 5.5 | V | |
| V _{IN} | Digital Select Input Voltage | GND | 5.5 | V | |
| V _{IS} | Analog Input Voltage (NC, NO, COM) | GND | V _{CC} | V | |
| T _A | Operating Temperature Range | -55 | +125 | °C | |
| t _r , t _f | Input Rise or Fall Time, SELECT | V _{CC} = 3.3 V ± 0.3 V | 0 | 100 | ns/V |
| | | V _{CC} = 5.0 V ± 0.5 V | 0 | 20 | |

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

| Junction Temperature °C | Time, Hours | Time, Years |
|-------------------------|-------------|-------------|
| 80 | 1,032,200 | 117.8 |
| 90 | 419,300 | 47.9 |
| 100 | 178,700 | 20.4 |
| 110 | 79,600 | 9.4 |
| 120 | 37,000 | 4.2 |
| 130 | 17,800 | 2.0 |
| 140 | 8,900 | 1.0 |

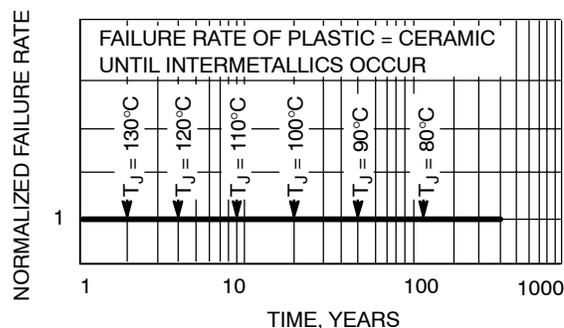


Figure 3. Failure Rate vs. Time Junction Temperature

NLAST44599

DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

| Symbol | Parameter | Condition | V _{CC} | Guaranteed Limit | | | Unit |
|------------------|---|---|-----------------|------------------|--------|---------|------|
| | | | | –55°C to 25°C | < 85°C | < 125°C | |
| V _{IH} | Minimum High-Level Input Voltage, Select Inputs | | 3.0 | 2.0 | 2.0 | 2.0 | V |
| | | | 4.5 | 2.0 | 2.0 | 2.0 | |
| | | | 5.5 | 2.0 | 2.0 | 2.0 | |
| V _{IL} | Maximum Low-Level Input Voltage, Select Inputs | | 3.0 | 0.5 | 0.5 | 0.5 | V |
| | | | 4.5 | 0.8 | 0.8 | 0.8 | |
| | | | 5.5 | 0.8 | 0.8 | 0.8 | |
| I _{IN} | Maximum Input Leakage Current | V _{IN} = 5.5 V or GND | 5.5 | ± 0.2 | ± 2.0 | ± 2.0 | μA |
| I _{OFF} | Power Off Leakage Current, Select Inputs | V _{IN} = 5.5 V or GND | 0 | ± 10 | ± 10 | ± 10 | μA |
| I _{CC} | Maximum Quiescent Supply Current | Select and V _{IS} = V _{CC} or GND | 5.5 | 4.0 | 4.0 | 8.0 | μA |

DC ELECTRICAL CHARACTERISTICS – Analog Section

| Symbol | Parameter | Condition | V _{CC} | Guaranteed Limit | | | Unit |
|--|---|--|-----------------|------------------|--------|---------|------|
| | | | | –55°C to 25°C | < 85°C | < 125°C | |
| R _{ON} | Maximum “ON” Resistance (Figures 17 – 23) | V _{IN} = V _{IL} or V _{IH} V _{IS} = GND to V _{CC} I _{IN} ≤ 10.0 mA | 2.5 | 85 | 95 | 105 | Ω |
| | | | 3.0 | 45 | 50 | 55 | |
| | | | 4.5 | 30 | 35 | 40 | |
| | | | 5.5 | 25 | 30 | 35 | |
| R _{FLAT (ON)} | ON Resistance Flatness (Figures 17 – 23) | V _{IN} = V _{IL} or V _{IH} I _{IN} ≤ 10.0 mA V _{IS} = 1 V, 2 V, 3.5 V | 4.5 | 4 | 4 | 5 | Ω |
| I _{NC(OFF)} I _{NO(OFF)} | NO or NC Off Leakage Current (Figure 9) | V _{IN} = V _{IL} or V _{IH} V _{NO} or V _{NC} = 1.0 V _{COM} 4.5 V | 5.5 | 1 | 10 | 100 | nA |
| I _{COM(ON)} | COM ON Leakage Current (Figure 9) | V _{IN} = V _{IL} or V _{IH} V _{NO} 1.0 V or 4.5 V with V _{NC} floating or V _{NO} 1.0 V or 4.5 V with V _{NO} floating V _{COM} = 1.0 V or 4.5 V | 5.5 | 1 | 10 | 100 | nA |

NLAST44599

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

| Symbol | Parameter | Test Conditions | V _{CC} (V) | V _{IS} (V) | Guaranteed Maximum Limit | | | | | | Unit | |
|------------------|--------------------------------------|--|------------------------|------------------------|--------------------------|------|-----|--------|-----|---------|------|-----|
| | | | | | - 55°C to 25°C | | | < 85°C | | < 125°C | | |
| | | | | | Min | Typ* | Max | Min | Max | Min | | Max |
| t _{ON} | Turn-On Time (Figures 12 and 13) | R _L = 300 Ω, C _L = 35 pF (Figures 5 and 6) | 2.5 | 2.0 | 5 | 23 | 35 | 5 | 38 | 5 | 41 | ns |
| | | | 3.0 | 2.0 | 5 | 16 | 24 | 5 | 27 | 5 | 30 | |
| | | | 4.5 | 3.0 | 2 | 11 | 16 | 2 | 19 | 2 | 22 | |
| | | | 5.5 | 3.0 | 2 | 9 | 14 | 2 | 17 | 2 | 20 | |
| t _{OFF} | Turn-Off Time (Figures 12 and 13) | R _L = 300 Ω, C _L = 35 pF (Figures 5 and 6) | 2.5 | 2.0 | 1 | 7 | 12 | 1 | 15 | 1 | 18 | ns |
| | | | 3.0 | 2.0 | 1 | 5 | 10 | 1 | 13 | 1 | 16 | |
| | | | 4.5 | 3.0 | 1 | 4 | 6 | 1 | 9 | 1 | 12 | |
| | | | 5.5 | 3.0 | 1 | 3 | 5 | 1 | 8 | 1 | 11 | |
| t _{BBM} | Minimum Break-Before-Make Time | V _{IS} = 3.0 V (Figure 4) R _L = 300 Ω, C _L = 35 pF | 2.5 | 2.0 | 1 | 12 | | 1 | | 1 | | ns |
| | | | 3.0 | 2.0 | 1 | 11 | | 1 | | 1 | | |
| | | | 4.5 | 3.0 | 1 | 6 | | 1 | | 1 | | |
| | | | 5.5 | 3.0 | 1 | 5 | | 1 | | 1 | | |

*Typical Characteristics are at 25°C.

| | | Typical @ 25, V _{CC} = 5.0 V | |
|------------------------------------|---|---------------------------------------|--|
| C _{IN} | Maximum Input Capacitance, Select Input | 8 | |
| C _{NO} or C _{NC} | Analog I/O (Switch Off) | 10 | |
| C _{COM} | Common I/O (Switch Off) | 10 | |
| C _(ON) | Feedthrough (Switch On) | 20 | |

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

| Symbol | Parameter | Condition | V _{CC} V | Typical | Unit |
|------------------|---|--|----------------------|---------|------|
| | | | | 25°C | |
| BW | Maximum On-Channel - 3 dB Bandwidth or Minimum Frequency Response (Figure 11) | V _{IN} = 0 dBm V _{IN} centered between V _{CC} and GND (Figure 7) | 3.0 | 145 | MHz |
| | | | 4.5 | 170 | |
| | | | 5.5 | 175 | |
| V _{ONL} | Maximum Feedthrough On Loss | V _{IN} = 0 dBm @ 100 kHz to 50 MHz V _{IN} centered between V _{CC} and GND (Figure 7) | 3.0 | -3 | dB |
| | | | 4.5 | -3 | |
| | | | 5.5 | -3 | |
| V _{ISO} | Off-Channel Isolation (Figure 10) | f = 100 kHz; V _{IS} = 1 V RMS V _{IN} centered between V _{CC} and GND (Figure 7) | 3.0 | -93 | dB |
| | | | 4.5 | -93 | |
| | | | 5.5 | -93 | |
| Q | Charge Injection Select Input to Common I/O (Figure 15) | V _{IN} = V _{CC} to GND, F _{IS} = 20 kHz t _r = t _f = 3 ns R _{IS} = 0 Ω, C _L = 1000 pF Q = C _L * ΔV _{OUT} (Figure 8) | 3.0 | 1.5 | pC |
| | | | 5.5 | 3.0 | |
| THD | Total Harmonic Distortion THD + Noise (Figure 14) | F _{IS} = 20 Hz to 100 kHz, R _L = R _{gen} = 600 Ω, C _L = 50 pF V _{IS} = 5.0 V _{PP} sine wave | 5.5 | 0.1 | % |
| VCT | Channel to Channel Crosstalk | f = 100 kHz; V _{IS} = 1 V RMS V _{IN} centered between V _{CC} and GND (Figure 7) | 5.5 | -90 | dB |
| | | | 3.0 | -90 | |

NLAST44599

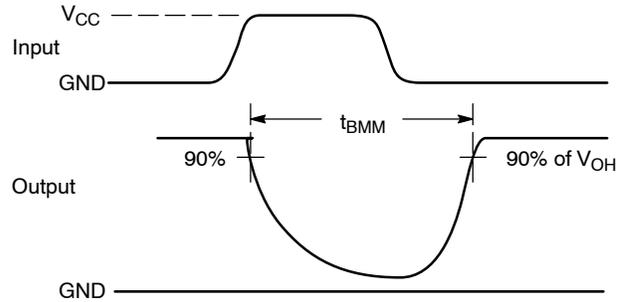
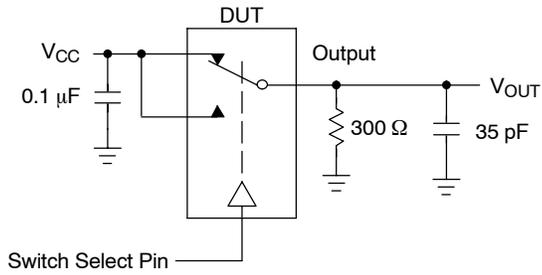


Figure 4. t_{BMM} (Time Break-Before-Make)

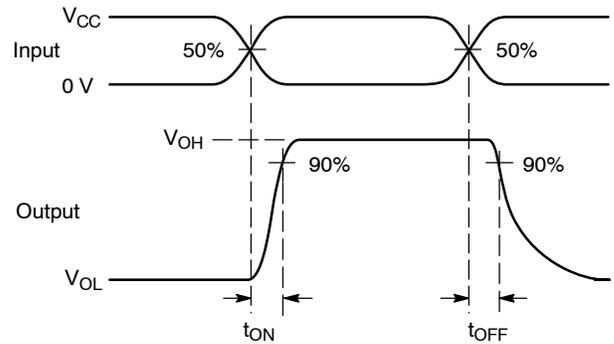
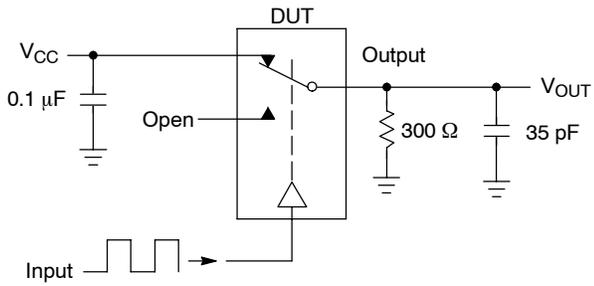


Figure 5. t_{ON}/t_{OFF}

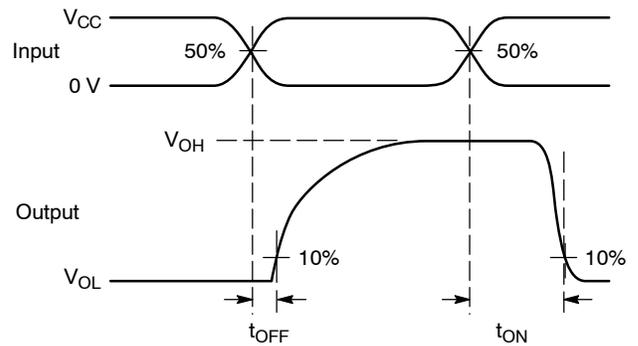
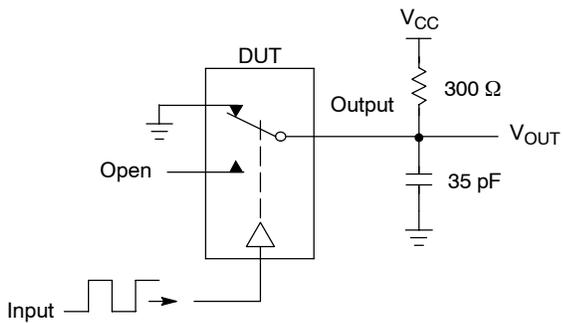
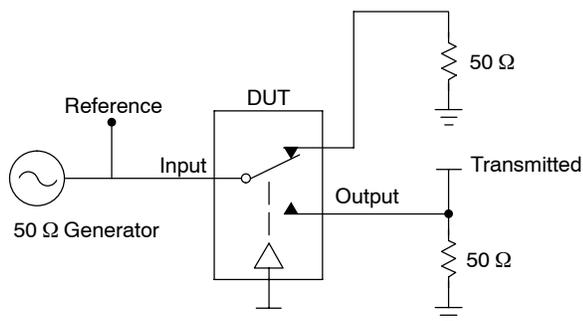


Figure 6. t_{ON}/t_{OFF}

NLAST44599



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz}$$

$$V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ V_{ONL}

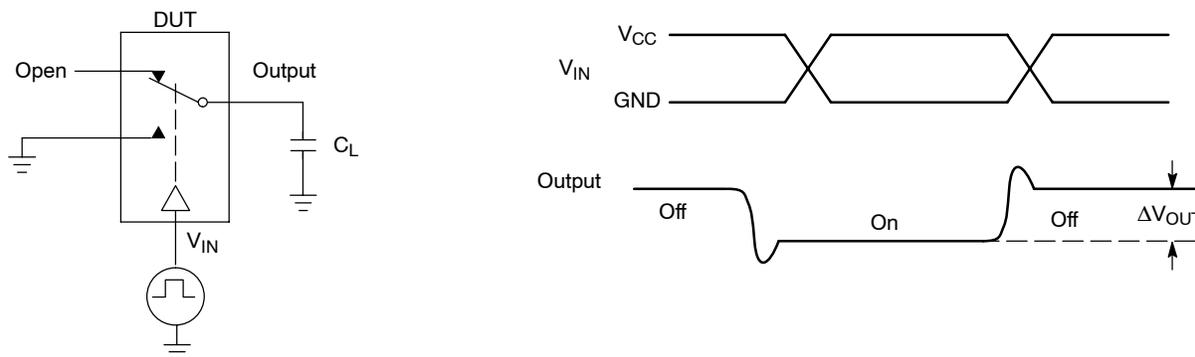


Figure 8. Charge Injection: (Q)

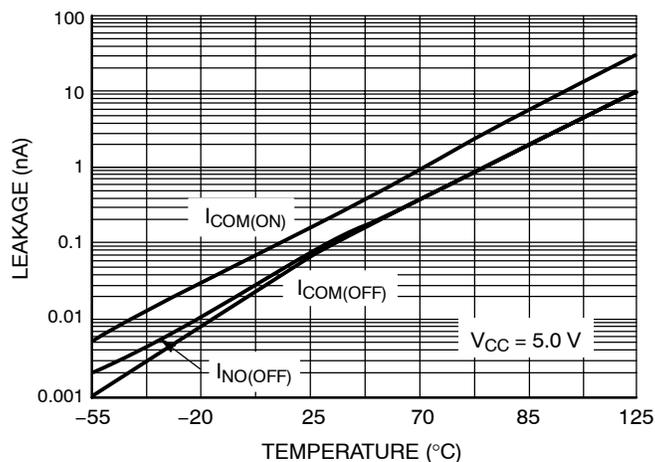


Figure 9. Switch Leakage vs. Temperature

NLAST44599

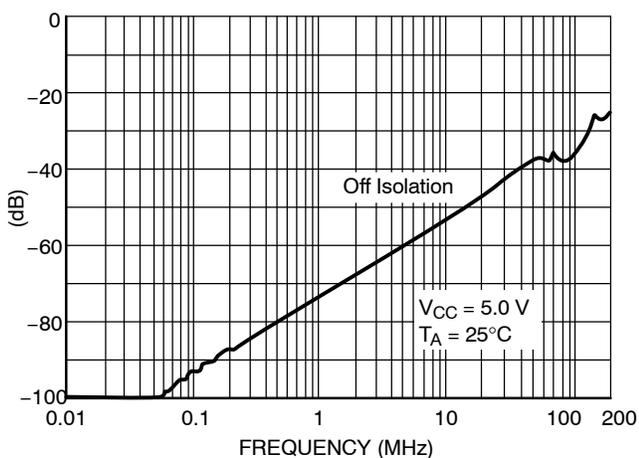


Figure 10. Off-Channel Isolation

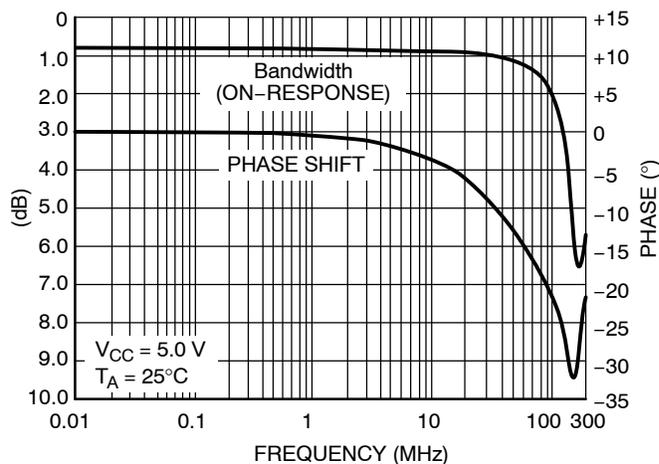


Figure 11. Typical Bandwidth and Phase Shift

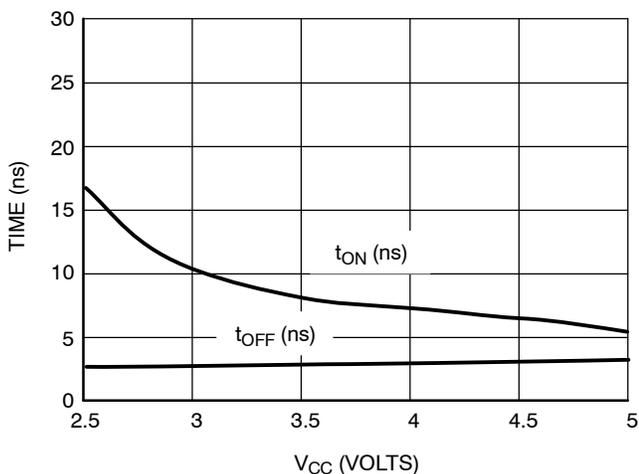


Figure 12. t_{ON} and t_{OFF} vs. V_{CC} at 25°C

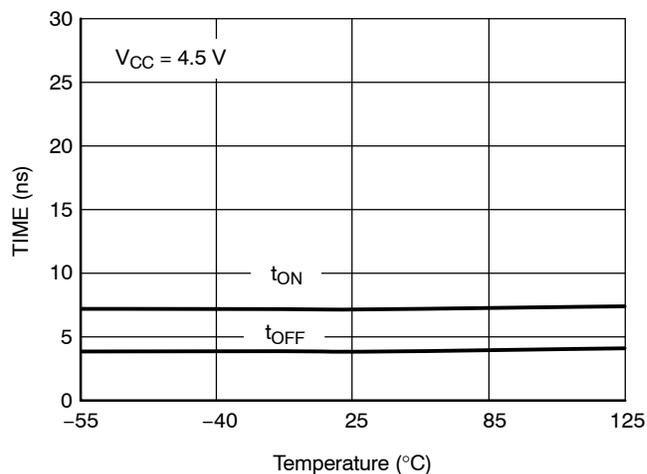


Figure 13. t_{ON} and t_{OFF} vs. Temp

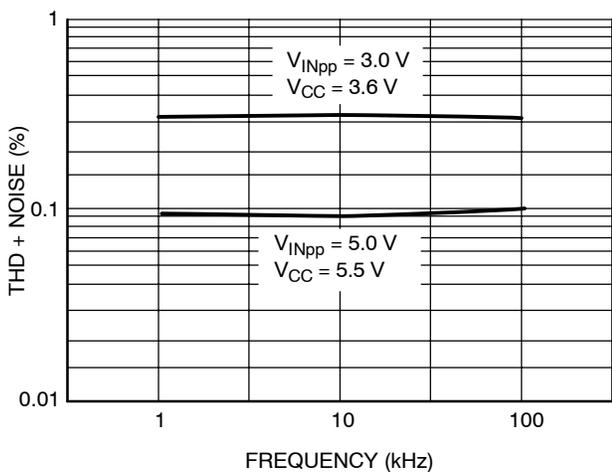


Figure 14. Total Harmonic Distortion Plus Noise vs. Frequency

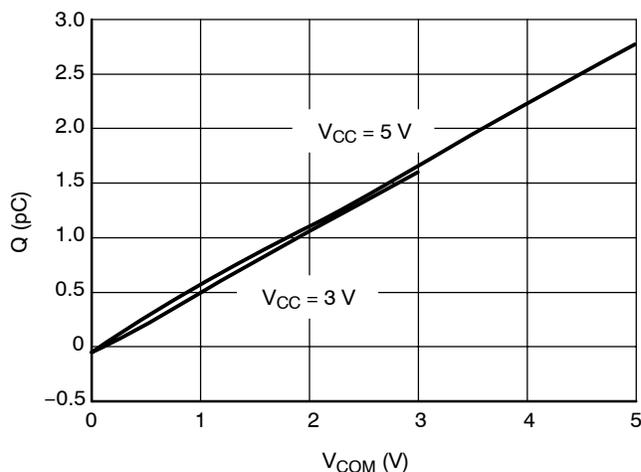


Figure 15. Charge Injection vs. COM Voltage

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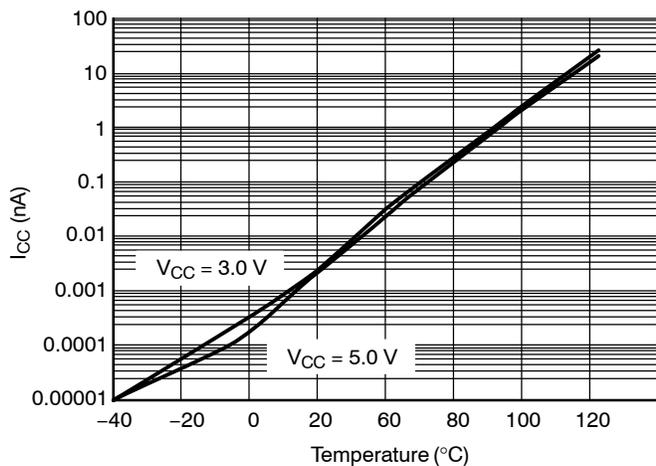


Figure 16. I_{CC} vs. Temp, $V_{CC} = 3\text{ V}$ and 5 V

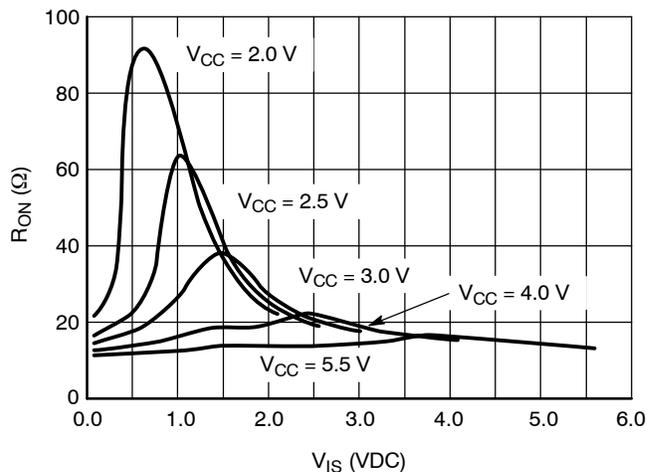


Figure 17. R_{ON} vs. V_{CC} , Temp = 25°C

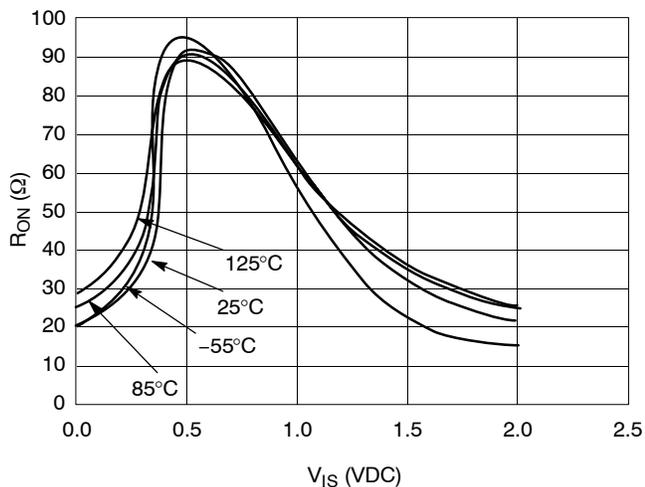


Figure 18. R_{ON} vs Temp, $V_{CC} = 2.0\text{ V}$

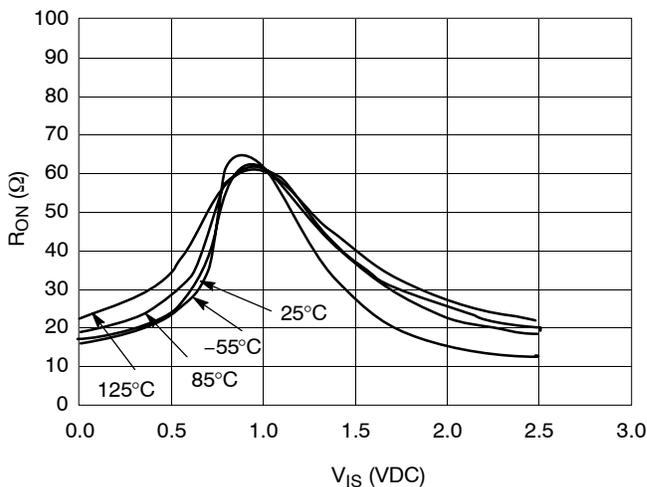


Figure 19. R_{ON} vs. Temp, $V_{CC} = 2.5\text{ V}$

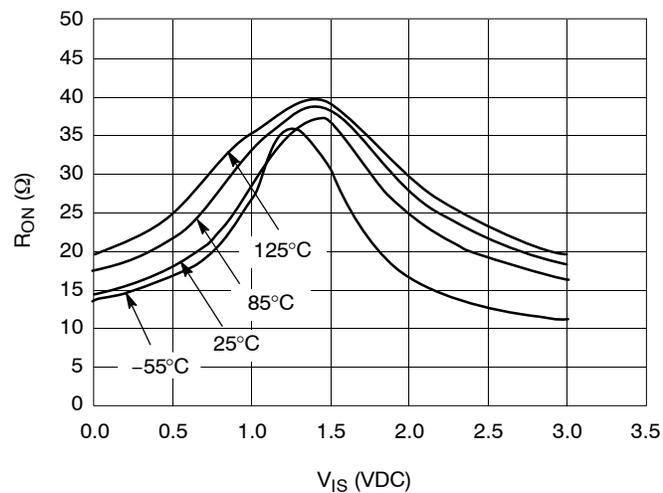


Figure 20. R_{ON} vs. Temp, $V_{CC} = 3.0\text{ V}$

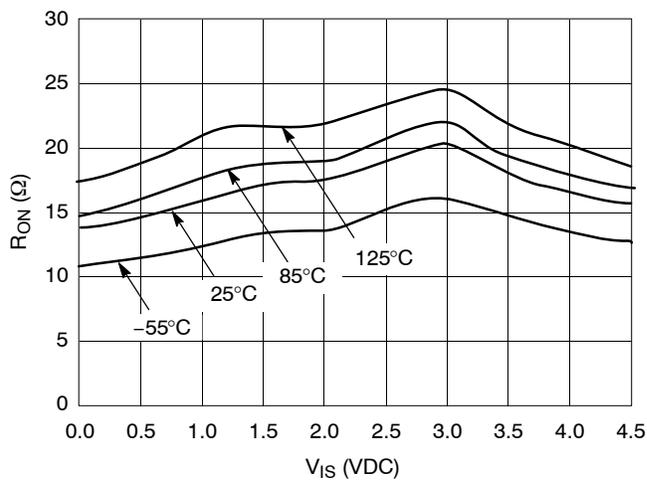


Figure 21. R_{ON} vs. Temp, $V_{CC} = 4.5\text{ V}$

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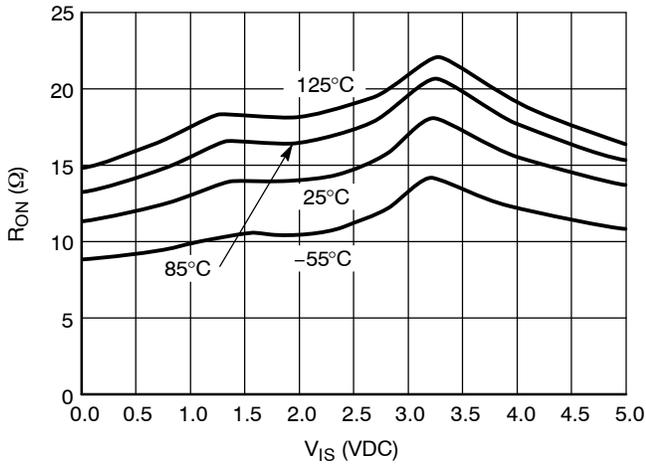


Figure 22. R_{ON} vs. Temp, $V_{CC} = 5.0$ V

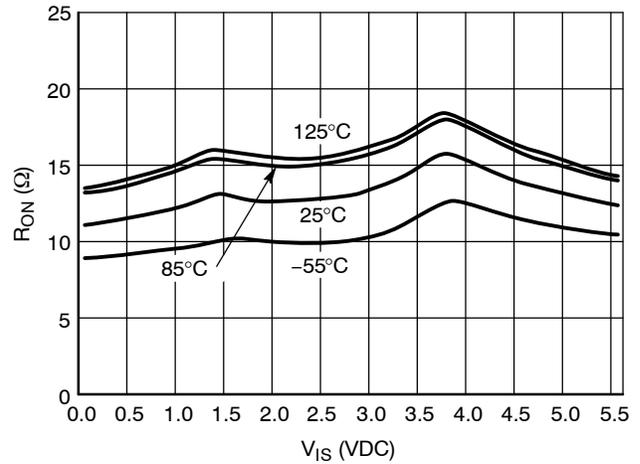


Figure 23. R_{ON} vs. Temp, $V_{CC} = 5.5$ V

DEVICE ORDERING INFORMATION

| Device Order Number | Device Nomenclature | | | | | Package Type | Shipping [†] |
|---------------------|---------------------|------------|-----------------|----------------|----------------------|------------------|-----------------------|
| | Circuit Indicator | Technology | Device Function | Package Suffix | Tape and Reel Suffix | | |
| NLAST44599DT | NL | AS | 44599 | DT | | TSSOP-16* | 96 Unit / Rail |
| NLAST44599DTR2 | NL | AS | 44599 | DT | R2 | TSSOP-16* | 2500 / Tape & Reel |
| NLAST44599MN | NL | AS | 44599 | MN | | QFN-16 | 124 Unit Rail |
| NLAST44599MNG | NL | AS | 44599 | MN | | QFN-16 (Pb-Free) | 124 Unit Rail |
| NLAST44599MNR2 | NL | AS | 44599 | MN | R2 | QFN-16 | 2500 / Tape & Reel |
| NLAST44599MNR2G | NL | AS | 44599 | MN | R2 | QFN-16 (Pb-Free) | 2500 / Tape & Reel |

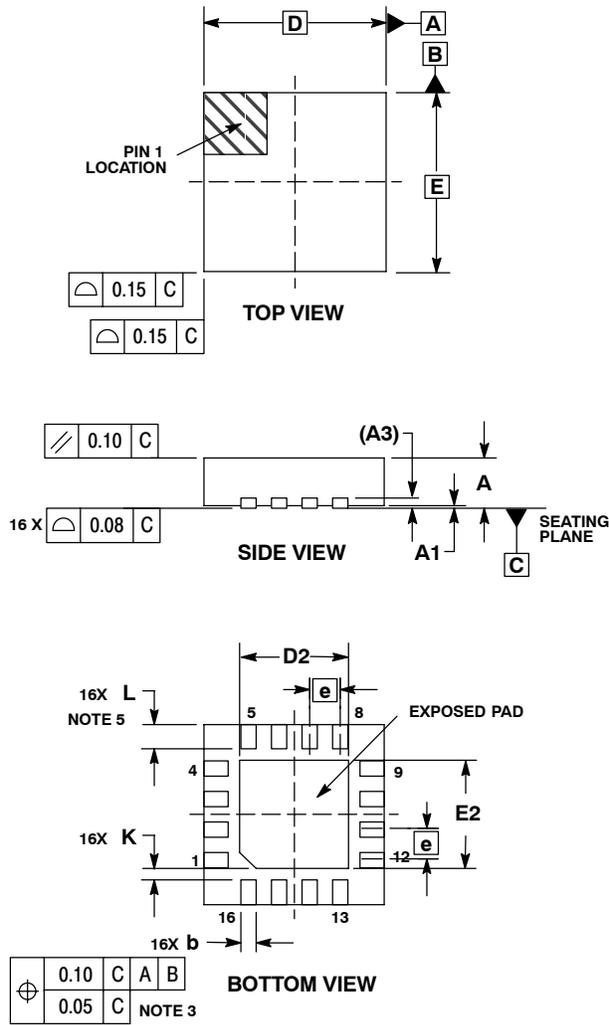
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

NLAST44599

PACKAGE DIMENSIONS

QFN-16
MN SUFFIX
CASE 485G-01
ISSUE B

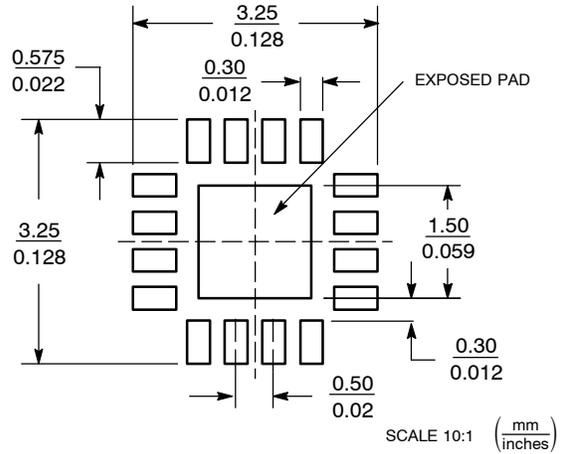


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. L_{max} CONDITION CAN NOT VIOLATE 0.2 MM MINIMUM SPACING BETWEEN LEAD TIP AND FLAG

| MILLIMETERS | | |
|-------------|------|------|
| DIM | MIN | MAX |
| A | 0.80 | 1.00 |
| A1 | 0.00 | 0.05 |
| A3 | 0.20 | REF |
| b | 0.18 | 0.30 |
| D | 3.00 | BSC |
| D2 | 1.65 | 1.85 |
| E | 3.00 | BSC |
| E2 | 1.65 | 1.85 |
| e | 0.50 | BSC |
| K | 0.20 | --- |
| L | 0.30 | 0.50 |

SOLDERING FOOTPRINT*

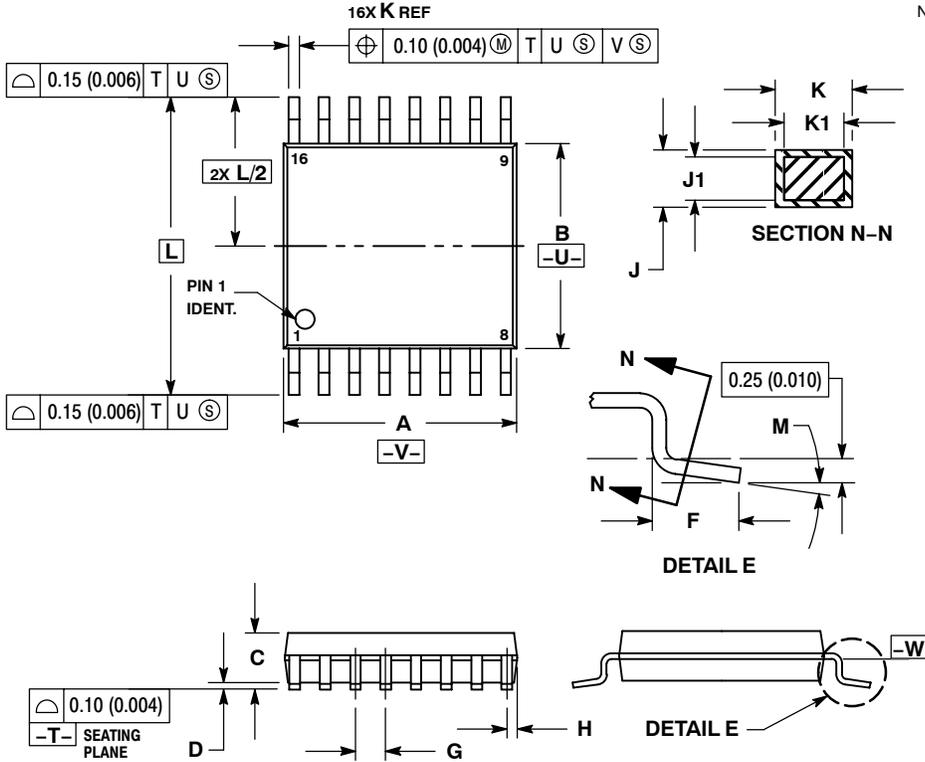


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NLAST44599

PACKAGE DIMENSIONS

TSSOP-16
CASE 948F-01
ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.90 | 5.10 | 0.193 | 0.200 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| C | --- | 1.20 | --- | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 BSC | | 0.026 BSC | |
| H | 0.18 | 0.28 | 0.007 | 0.011 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 BSC | | 0.252 BSC | |
| M | 0° | 8° | 0° | 8° |

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